Elektronische Bauelemente

SGM0410S-C

2.2A, 100V, $R_{DS(ON)}$ 310mΩ
N-Channel Enhancement Mode Power MOSFET

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

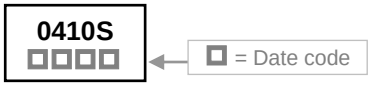
The SGM0410S-C is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The SGM0410-C meet the RoHS and Green Product requirement with full function reliability approved.

FEATURES

- Lower Gate Charge
- Simple Drive Requirement
- Fast Switching Characteristic

MARKING



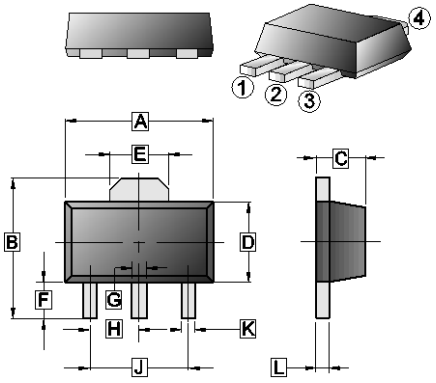
PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-89	1K	7 inch

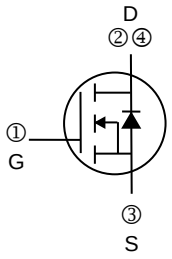
ORDER INFORMATION

Part Number	Type
SGM0410S-C	Lead (Pb)-free and Halogen-free

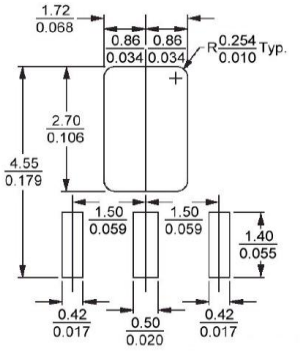
SOT-89



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.60	G	0.40	0.58
B	3.94	4.25	H	1.50 TYP.	
C	1.40	1.60	J	3.00 TYP.	
D	2.25	2.60	K	0.32	0.52
E	1.55 TYP.		L	0.35	0.44
F	0.89	1.20			



Mounting Pad Layout



*Dimensions in millimeters

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1] @V_{GS}=10V	T_A=25°C	I_D	2.2	A
	T_A=70°C		1.7	A
Pulsed Drain Current [2]		I_{DM}	5.5	A
Power Dissipation [3]	T_A=25°C	P_D	1.5	W
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Thermal Resistance Rating				
Maximum Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	85	°C/W
Maximum Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	36	

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage		BV_{DSS}	100	-	-	V	V_{GS}=0, I_D= 250μA
Gate-Threshold Voltage		$V_{GS(th)}$	1	-	2.5	V	V_{DS}=V_{GS}, I_D=250μA
Forward Transconductance		g_{fs}	-	5.4	-	S	V_{DS}=5V, I_D=2A
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±20V, V_{DS}=0
Drain-Source Leakage Current	T_J=25°C	I_{DSS}	-	-	1	μA	V_{DS}=80V, V_{GS}=0
	T_J=55°C		-	-	5		
Static Drain-Source On-Resistance [2]		$R_{DS(ON)}$	-	260	310	mΩ	V_{GS}=10V, I_D=2A
			-	270	320		V_{GS}=4.5V, I_D=1A
Gate Resistance		R_g	-	2.8	5.6	Ω	V_{GS}=V_{DS}=0, f=1MHz
Total Gate Charge (10V)		Q_g	-	9.1	-	nC	I_D=2A V_{DS}=50V V_{GS}=10V
Gate-Source Charge		Q_{gs}	-	2	-		
Gate-Drain Change		Q_{gd}	-	1.4	-		
Turn-on Delay Time [2]		$T_{d(on)}$	-	2	-	nS	V_{DD}=50V I_D=2A V_{GS}=10V R_G=3.3Ω
Rise Time		T_r	-	21.6	-		
Turn-off Delay Time		$T_{d(off)}$	-	11.2	-		
Fall Time		T_f	-	18.8	-		
Input Capacitance		C_{iss}	-	508	-	pF	V_{GS}=0 V_{DS}=15V f=1MHz
Output Capacitance		C_{oss}	-	29	-		
Reverse Transfer Capacitance		C_{rss}	-	16.4	-		
Source-Drain Diode							
Diode Forward Voltage [2]		V_{SD}	-	-	1.2	V	I_S=1A, V_{GS}=0, T_J=25°C
Continuous Source Current [1,4]		I_S	-	-	2.2	A	V_D=V_G=0, Force Current
Pulsed Source Current [2,4]		I_{SM}	-	-	5.5	A	
Reverse Recovery Time		T_{rr}	-	17.5	-	nS	I_F=2A, dI/dt=100A/μs, T_J=25°C
Reverse Recovery Charge		Q_{rr}	-	14	-	nC	

Notes:
1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2oz copper.
2. The data tested by pulsed, pulse width≦ 300μs, duty cycle≦ 2%.
3. The power dissipation is limited by 150°C, junction temperature.
4. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

CHARACTERISTIC CURVES

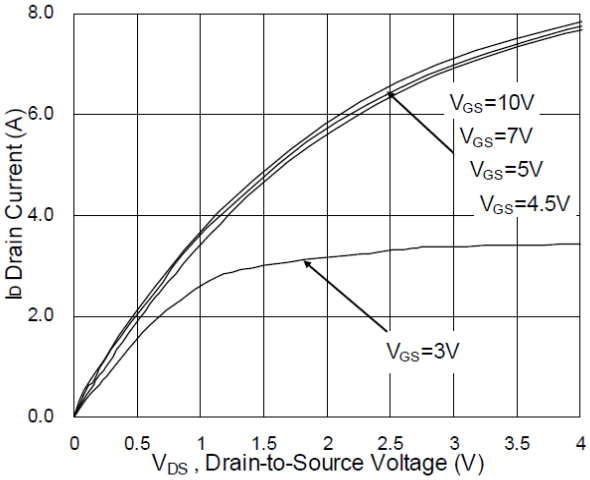


Fig.1 Typical Output Characteristics

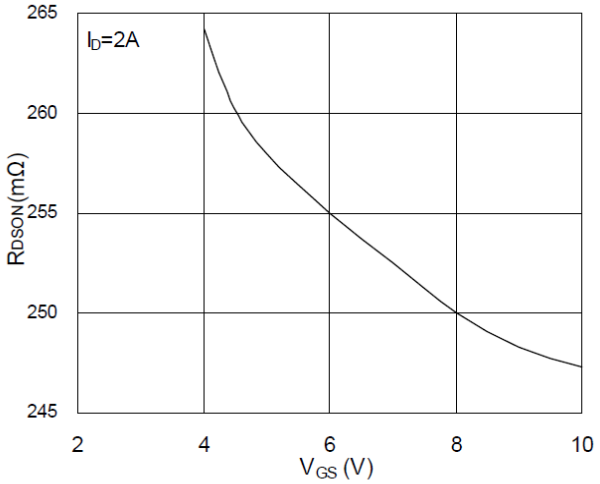


Fig.2 On-Resistance vs. Gate-Source

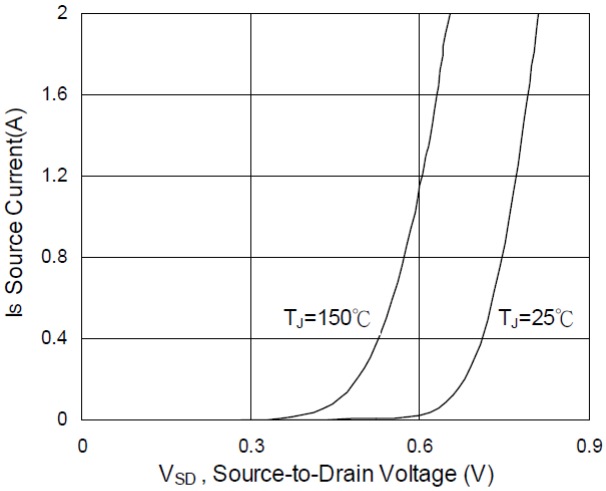


Fig.3 Forward Characteristics of Reverse

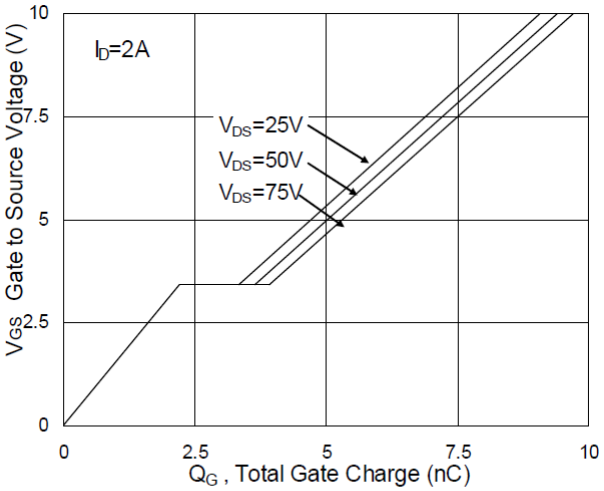


Fig.4 Gate-Charge Characteristics

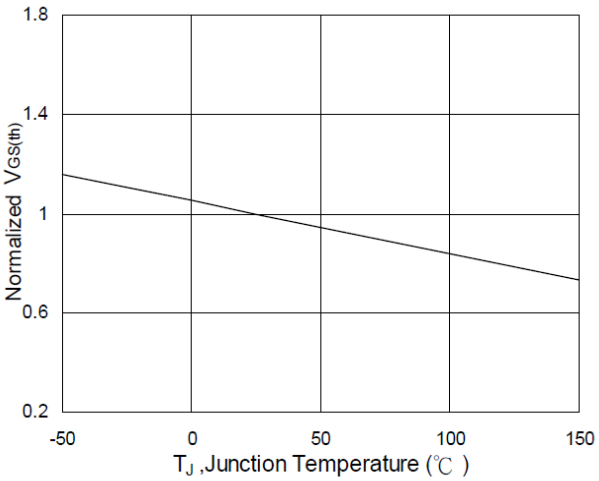


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

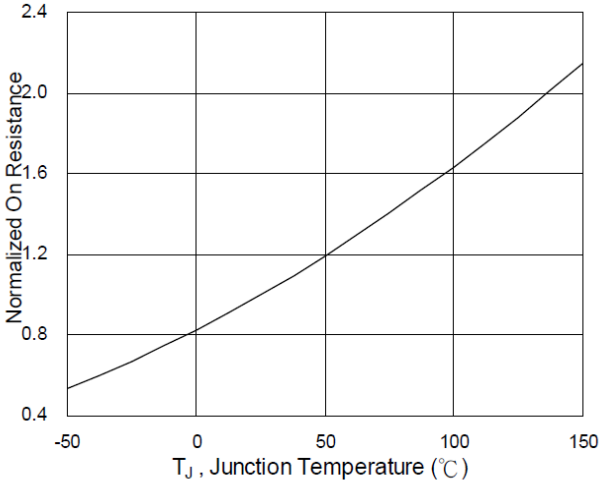


Fig.6 Normalized R_{DSON} vs. T_J

CHARACTERISTIC CURVES

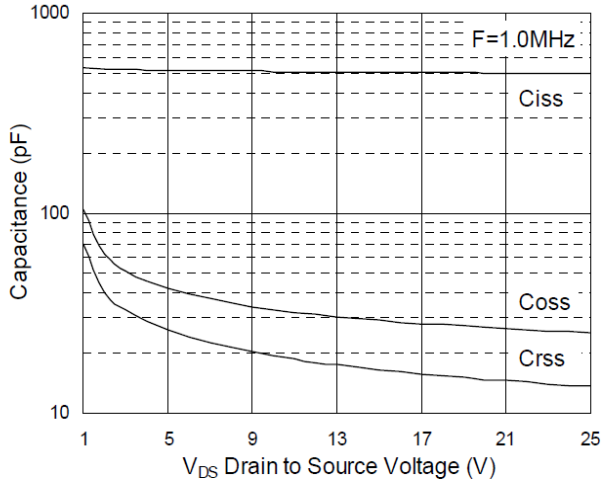


Fig.7 Capacitance

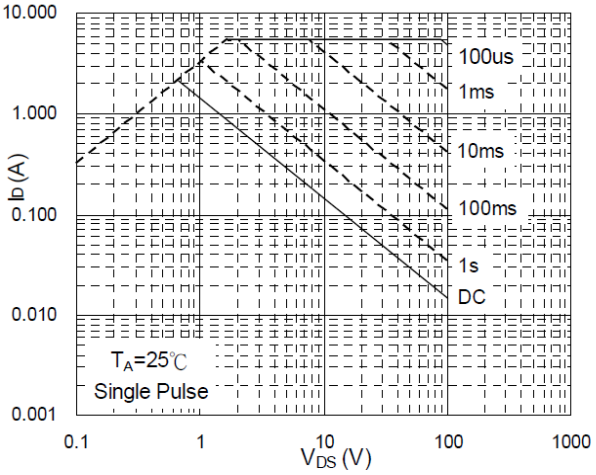


Fig.8 Safe Operating Area

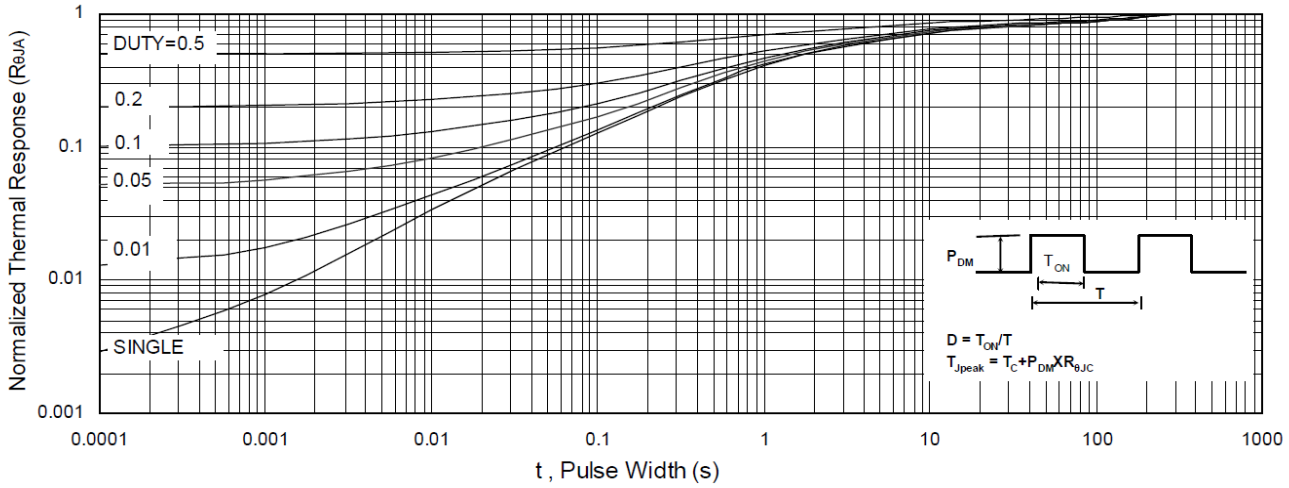


Fig.9 Normalized Maximum Transient Thermal Impedance

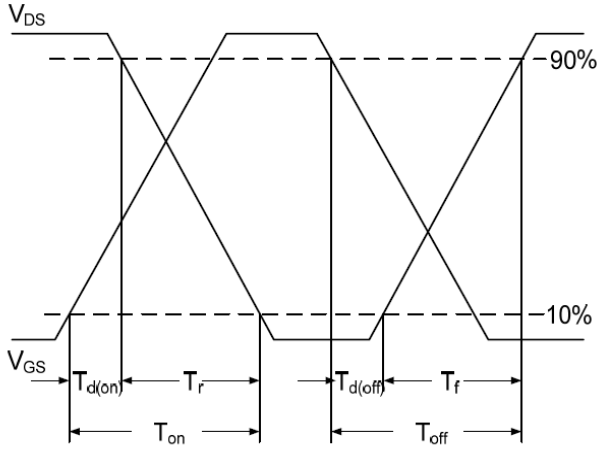


Fig.10 Switching Time Waveform

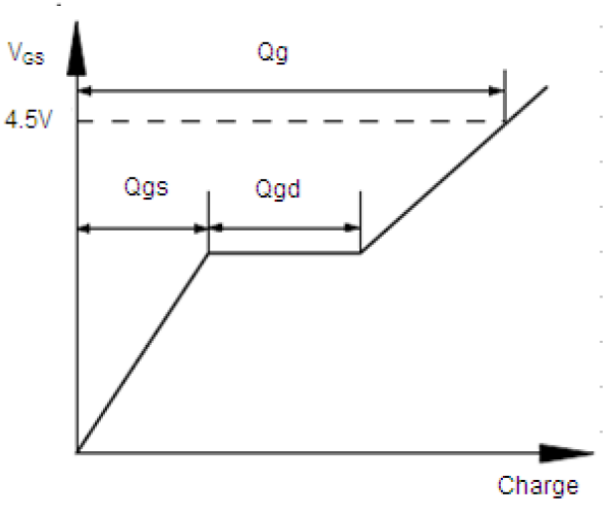


Fig.11 Gate Charge Waveform